Central™
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2N3467
2N3468

PNP SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3467, 2N3468 types are Silicon PNP Switching Transistors designed for core driver applications

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N3467	2N3468	UNIT
Collector-Base Voltage	V_{CBO}	40	50	V
Collector-Emitter Voltage	V_{CEO}	40	50	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Collector Current	I_C	1.0		A
Power Dissipation	P_D	1.0		W
Power Dissipation (T_C=25°C)	P_D	5.0		W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +200		°C
Thermal Resistance	Θ_{JA}	175		°C/W
Thermal Resistance	Θ_{JC}	35		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

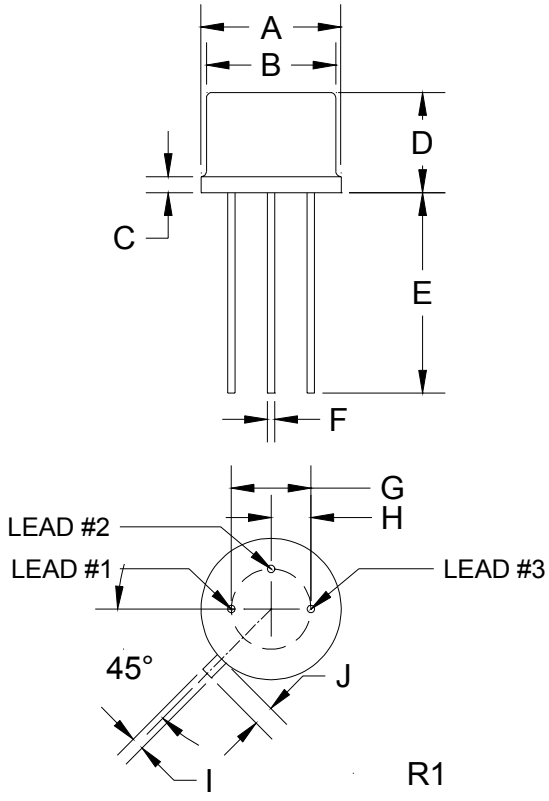
		2N3467		2N3468		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNIT
I_{CBO}	V_{CB}=30V		0.1		0.1	µA
I_{CBO}	V_{CB}=30V, T_A=100°C		15		15	µA
I_{CEV}	V_{CE}=30V, V_{BE}=3.0V		100		100	nA
I_{BEV}	V_{CE}=30V, V_{BE}=3.0V		120		120	nA
BV_{CBO}	I_C=10µA	40		50		V
BV_{CEO}	I_C=10mA	40		50		V
BV_{EBO}	I_E=10µA	5.0		5.0		V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA		0.3		0.36	V
$V_{CE(SAT)}$	I_C=500mA, I_B=50mA		0.5		0.6	V
$V_{CE(SAT)}$	I_C=1.0A, I_B=100mA		1.0		1.2	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA		1.0		1.0	V
$V_{BE(SAT)}$	I_C=500mA, I_B=50mA	0.8	1.2	0.8	1.2	V
$V_{BE(SAT)}$	I_C=1.0A, I_B=100mA		1.6		1.6	V

(SEE REVERSE SIDE)

ELECTRICAL CHARACTERISTICS (Continued)

SYMBOL	TEST CONDITIONS	2N3467 MIN	2N3467 MAX	2N3468 MIN	2N3468 MAX	UNITS
h_{FE}	V_{CE}=1.0V, I_C=150mA	40		25		
h_{FE}	V_{CE}=1.0V, I_C=500mA	40	120	25	75	
h_{FE}	V_{CE}=5.0V, I_C=1.0A	40		20		
f_T	V_{CE}=10V, I_C=50mA, f=100MHz	175		150		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=100kHz		25		25	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=100kHz		100		100	pF
t_{ON}	V_{CC}=30V, VBE=2.0V, I_C=500mA, I_{B1}=50mA		40		40	ns
t_{OFF}	V_{CC}=30V, I_C=500mA, I_{B1}=I_{B2}=50mA		90		90	ns
QT	V_{CC}=30V, I_C=500mA, I_B=50mA		6.0		6.0	nC

TO-39 CASE - MECHANICAL DIMENSIONS



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

Lead Code:

1) Emitter
2) Base
3) Collector

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